TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

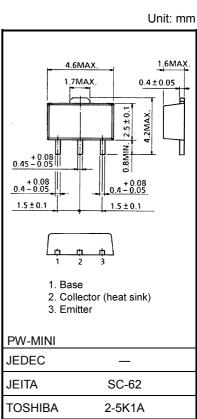
# 2SA1735

## **Power Amplifier Applications Power Switching Applications**

- Low saturation voltage:  $V_{CE}$  (sat) = -0.5 V (max) (I<sub>C</sub> = -500 mA) •
- High speed switching time:  $t_{stg} = 0.25 \ \mu s \ (typ.)$
- Small flat package
- $P_C = 1.0$  to 2.0 W (mounted on ceramic substrate)
- Complementary to 2SC4540

### Maximum Ratings (Ta = 25°C)

| Characteristics             | Symbol           | Rating     | Unit |  |
|-----------------------------|------------------|------------|------|--|
| Collector-base voltage      | V <sub>CBO</sub> | -60        | V    |  |
| Collector-emitter voltage   | V <sub>CEO</sub> | -50        | V    |  |
| Emitter-base voltage        | V <sub>EBO</sub> | -6         | V    |  |
| Collector current           | Ι <sub>C</sub>   | -1         | А    |  |
| Base current                | Ι <sub>Β</sub>   | -0.2       | А    |  |
| Collector power dissipation | P <sub>C</sub>   | 500        | mW   |  |
|                             | P <sub>C</sub>   | 1000       |      |  |
|                             | (Note)           | 1000       |      |  |
| Junction temperature        | Тј               | 150        | °C   |  |
| Storage temperature range   | T <sub>stg</sub> | -55 to 150 | °C   |  |



Weight: 0.05 g (typ.)

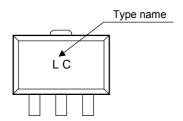
Note: Mounted on ceramic substrate (250 mm<sup>2</sup> × 0.8 t)



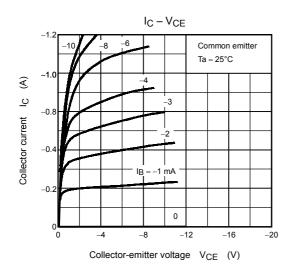
Electrical Characteristics (Ta = 25°C)

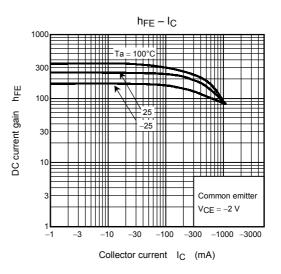
| Charac                       | teristics         | Symbol                | Test Condition  | Min | Тур. | Max  | Unit |
|------------------------------|-------------------|-----------------------|---|-----|------|------|------|
| Collector cut-off cu         | rrent             | I <sub>CBO</sub>      | $V_{CB} = -60 \text{ V}, \text{ I}_{E} = 0$   | —   | _    | -0.1 | μA   |
| Emitter cut-off curre        | ent               | I <sub>EBO</sub>      | $V_{EB} = -6 V, I_C = 0$  | _   | _    | -0.1 | μA   |
| Collector-emitter br         | eakdown voltage   | V (BR) CEO            | I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0   | -50 |      | _    | V    |
| DC current gain              |                   | h <sub>FE (1)</sub>   | $V_{CE} = -2 V, I_C = -100 mA$  | 120 | _    | 400  |      |
|                              |                   | h <sub>FE (2)</sub>   | V <sub>CE</sub> = -2 V, I <sub>C</sub> = -700 mA  | 40  | _    | _    |      |
| Collector-emitter sa         | aturation voltage | V <sub>CE (sat)</sub> | I <sub>C</sub> = -500 mA, I <sub>B</sub> = -25 mA   | _   | _    | -0.5 | V    |
| Base-emitter satura          | ation voltage     | V <sub>BE (sat)</sub> | I <sub>C</sub> = -500 mA, I <sub>B</sub> = -25 mA   | _   | _    | -1.2 | V    |
| Transition frequency         |                   | fT                    | V <sub>CE</sub> = -2 V, I <sub>C</sub> = -100 mA  | _   | 100  | _    | MHz  |
| Collector output capacitance |                   | C <sub>ob</sub>       | V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz  | _   | 16   | _    | pF   |
| Switching time               | Turn-on time      | t <sub>on</sub>       | $I_{B1} \bigoplus I_{B2} \qquad OUTPUT$ $I_{B1} \bigoplus I_{B1} \bigoplus I$ | _   | 0.1  | _    |      |
|                              | Storage time      | t <sub>stg</sub>      |   | _   | 0.25 | _    | μs   |
|                              | Fall time         | t <sub>f</sub>        |   | _   | 0.1  | _    |      |

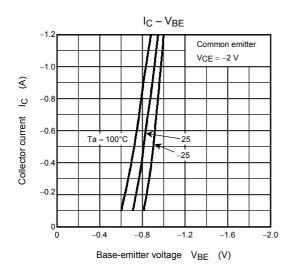
# Marking

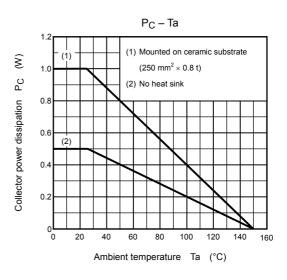


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